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Application Number	10581940
Filing Date	2006-06-07
First Named Inventor	Tetsuo Fujii et al.
Art Unit	2815
Examiner Name	Jerome Jackson Jr.
Attorney Docket Number	30794.108-US-WO

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	4	6277665		2001-08-21	Ma et al.	
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	6	6657236		2003-12-02	Thibeault et al.	
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	3	HWANG et al., "Efficient wet etching of GaN and p-GaN assisted with chopped UV source," Superlattices and Microstructures 35, 2004, pp. 45-57.	<input type="checkbox"/>

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4	SCHNITZER et al., "30% external quantum efficiency from surface textured, thin-film light-emitting diodes," <i>Appl. Phys. Lett.</i> 63 (16), 18 October 1993, pp. 2174-2176.	<input type="checkbox"/>
5	YAMADA et al., "InGaN-based near-ultraviolet and blue-light-emitting diodes with high external quantum efficiency using a patterned sapphire substrate and a mesh electrode," <i>Jpn. J. Appl. Phys.</i> , vol. 41, 2002, pp. L1431-L1433.	<input type="checkbox"/>
6	QI et al., "Study on the formation of dodecagonal pyramid on nitrogen polar GaN surface etched by hot H ₃ PO ₄ ," <i>Applied Physics Letters</i> , 95, 2009, pp. 071114-1-071114-3.	<input type="checkbox"/>
7	SHCHEKIN et al., "High performance thin-film flip-chip InGaN-GaN light-emitting diodes," <i>Applied Physics Letters</i> 89, 2006, 071109-1-071109-3.	<input type="checkbox"/>
8	HARLE et al., "Advanced technologies for high efficiency GaInN LEDs for solid state lighting," <i>Third International Conference on Solid State Lighting, Proceedings of the SPIE</i> , vol. 5187, 2004, pp. 34-40 (English Abstract only).	<input type="checkbox"/>

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